

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(minh near loan near tran) and ((n-type n adj type n adj channel n-channel n adj conductivity) or (p-type p adj type p adj channel p-channel p adj conductivity)) same (field near effect near transistor fet transistor and active and (@ad<"20020912" @rlad<"20020912"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 13:32
		same near conductivity near type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 12:16
L1	3081	257/291,292,226,e27.133.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 12:17
S1	2016	257/291-294,222.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:21
S2	4398	257/291-294,222,223,229,232,233, 235-238.ccls. or 348/308.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:17
S3	3567	(257/291-294,222,223,229,232,233, 235-238.ccls. or 348/308.ccls.) and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:17
S4	132	S3 and solid\$1state and imaging and photodiode and photoelectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:18

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S5	98	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:18
S6	97	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:18
S7	48	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:19
S8	15	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:19
S9	9	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:19
S10	9	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies and channel and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:19
S11	9	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies and channel and substrate and region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:19
S12	9	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies and channel and substrate and region and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:20

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S13	4	S3 and solid\$1state and imaging and photodiode and photoelectric and transistors and signal and charge and drive and circuit and amplifies and channel and substrate and region and pixel and active and generate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:22
S14	2	("5698902").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/22 15:24
S15	2	("5946563").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/22 15:39
S16	2	("6184516").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/22 15:25
S17	0	("8236767").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/22 15:43
S18	59	(yuzurihara near hiroshi).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:44
S19	16	(yuzurihara near hiroshi).in. and conversion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:48
S20	3	2001-111022	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:44

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S21	5	("5159256" "6104162" "6243276").PN. OR ("6566843").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 15:45
S22	56	(yuzurihara near hiroshi).in. and canon.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 15:50
S23	20	(yuzurihara near hiroshi).in. and canon.as.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 15:51
S24	17	(yuzurihara near hiroshi).in. and canon.as. and @ad<"20020912"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 12:47
S25	3	(yuzurihara near hiroshi).in. and canon.as. and @ad>"20020912"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 12:48
S26	5	(yuzurihara near hiroshi).in. and canon.as. and @ad<"20020912" and photoelectric	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 14:39
S27	2	("20060007336").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 15:10
S28	0	("2006/0007336").URPN.	USPAT	OR	ON	2006/02/23 14:40
S29	4837	canon.as. and @ad<"20020912" and photoelectric near conversion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 15:12
S30	199	canon.as. and @ad<"20020912" and photoelectric near conversion and hiroshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 15:13
S31	106	canon.as. and @ad<"20020912" and photoelectric near conversion and hiroshi.in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 15:13
S32	3	canon.as. and @ad<"20020912" and (photoelectric near conversion).ti. and hiroshi.in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 15:14
S33	106	canon.as. and @ad<"20020912" and photoelectric near conversion and hiroshi.in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/23 15:15

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S34	2	canon.as. and @ad<"20020912" and photoelectric near conversion and (yuzurihara near hiroshi).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 14:02
S35	0	"2000232108"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 14:02
S36	0	"22307899"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 14:02
S37	0	"00306637.0"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 14:02
S38	2	"00306637"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 14:03
S39	0	"00306637.0"	US-PGPUB; USPAT; USOCR; EPO	OR	ON	2006/02/24 14:03
S40	30	(yuzurihara near hiroshi).in. and canon.as.	US-PGPUB; USPAT; USOCR; EPO	OR	ON	2006/02/24 14:05
S41	6	((("5698844") or ("5861620") or ("5955753")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 21:34
S42	2	("5698844").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 14:56
S43	1199	n near channel same shift near register and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 14:58
S44	94550	n near channel near "10" shift near register and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 14:58

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S45	378	(n\$1channel) near10 (shift near register) and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 14:59
S46	41	(n\$1channel near MOS) near10 (shift near register) and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:03
S47	9	("1075028").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:47
S48	0	("s45andgatenearwidth").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:48
S49	378	(n\$1channel) near10 (shift near register) and @ad<"20020912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 17:48
S50	10	S49 and gate near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 17:51
S51	111	mosfet same gate near width same n\$channel and @ad<"20020912"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 18:53
S52	0	mosfet same gate near lenght same n\$channel and @ad<"20020912"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/24 18:53
S53	173	mosfet same gate near length same n\$channel and @ad<"20020912"	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/16 18:09
S54	145	mosfet same gate near length same n\$channel and @ad<"20020912"	USPAT	OR	ON	2006/02/24 18:54
S55	128	mosfet same gate near length same n\$channel and @ad<"20020912" and substrate	USPAT	OR	ON	2006/02/24 18:54

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S56	92	mosfet same gate near length same n\$channel and @ad<"20020912" and substrate and n\$1type and transistor	USPAT	OR	ON	2006/02/24 18:55
S57	74	mosfet same gate near length same n\$channel and @ad<"20020912" and substrate and n\$1type and transistor and mos	USPAT	OR	ON	2006/02/24 18:55
S58	6	((("5698844") or ("5861620") or ("5955753"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 21:34
S59	3	S58 and camera	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 21:34
S60	95702	(image near sensor) or (solid near state near imaging)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:21
S61	342386	photodidoe or photodetectro or photosensor or photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:23
S62	260	((MOS near fet) or MOSFET or (MOS near transistor)) same ((channel near polarity) or (channel near conductivity near type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:22
S63	316865	(driv\$3 near circuit) or (peripheral near circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:23
S64	428759	photodiode or photodetectro or photosensor or photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:23

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S65	509385	photodiode or photodetector or photosensor or photosensitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:24
S66	1	S60 and S65 and S62 and S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:31
S67	3736	S60 and S65 and S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:24
S68	571	((MOS near FET) or MOSFET or (MOS near transistor)) and ((channel near polarity) or (channel near conductivity near type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:25
S69	2	S67 and S68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:26
S70	177325	(MOS near FET) or MOSFET or (MOS near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:26
S71	781	S67 and S70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:27
S72	3641	257/222,233,291,292,294,E27.133.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:27

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S73	2	channel near polarity with S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:33
S74	113	channel near polarity with "same"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:34
S75	1	channel near polarity with "same" and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:34
S76	2647	channel with "same" and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:34
S77	292019	"257"/\$.ccls. and (@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:35
S78	2888	S72 and (@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 12:35
S79	217	S78 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:13
S80	13172	"same" near conductivity near type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:14

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S81	91502	"same" near (conductivity near type channel polarity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:14
S82	7557	"same" near (conductivity near type channel polarity) with transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:14
S83	4	"same" near (conductivity near type channel polarity) with transistor same drive and imaging	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:16
S84	3641	257/222,233,291,292,294,E27.133. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:17
S85	292019	"257"/\$.ccls. and (@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:54
S86	25	"same" near (conductivity near type channel polarity) with transistor and S84 and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:23
S87	0	"same" near (conductivity near type channel polarity) with transistor same "all" and S84 and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:19
S88	0	"same" near (conductivity near type channel polarity) with transistor same "all" and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:20

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S89	0	"same" near (conductivity near type channel polarity) same transistor same "all" and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:20
S90	9	"all" with (n\$1channel p\$1channel n\$1type p\$type "same" near channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:26
S91	0	"all" with (n\$1channel p\$1channel n\$1type p\$type "same" near channel) and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:24
S92	10	"all" with transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:26
S93	35	(minh near loan near tran).xa.xp. and "same" same channel near polarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:29
S94	39	(minh near loan near tran).xa.xp.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:29
S95	35	(minh near loan near tran).xa.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:29
S96	917	(minh near loan near tran).xp.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:29

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S97	131	(S95 or S96) and "same" with channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:44
S98	95702	(image near sensor) or (solid near state near imaging)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:45
S99	294479	S85 "same" near2 (polarity type) and S98	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 13:55
S10 0	670	S85 and "same" near2 (polarity type) and S98	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:46
S10 1	172	S85 and "same" near2 (polarity type) and S98 and transistor and channel and drive and image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:08
S10 2	23215718	(@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:54
S10 3	0	"328" and "same" near2 (polarity type) and transistor and number near process near required	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:55
S10 4	0	"l28" and "same" near2 (polarity type) and transistor and number near process near required	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:56

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S10 5	21	S102 and "same" near2 (polarity type) and transistor and number near process near required	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 16:57
S10 6	2394	n-channel near (MOS transistor FET field near effect near transistor MOS near type) and (image imaging) and (drive driver) and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:12
S10 7	61	n-channel near (MOS transistor FET field near effect near transistor MOS near type) same (image imaging) same (drive driver) and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 13:55
S10 8	32629	"all"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:23
S10 9	0	"all" with n-channel near (MOS transistor FET field near effect near transistor MOS near type) same (image imaging) same (drive driver) and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:27
S11 0	2	("4870441").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/16 18:27
S11 1	0	S110 and all	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:28
S11 2	0	S110 and "all"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 18:28

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S11 3	23216378	(@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 13:55
S11 4	2	("4870441").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/17 13:55
S11 5	1	n-channel near (MOS transistor FET field near effect near transistor MOS near type) same (image imaging) same (drive driver) and S113 and S114	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 13:56
S11 6	0	minh near loand near tran and (tft thin near film near transistor) and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 13:25
S11 7	69	minh near loan near tran and (tft thin near film near transistor) and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 13:25
S11 8	69	(minh near loan near tran) and (tft thin near film near transistor) and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 13:29
S11 9	119	(minh near loan near tran) and ((n-type n adj type n adj channel n-channel n adj conductivity) or (p-type p adj type p adj channel p-channel p adj conductivity)) same (field near effect near transistor fet transistor) and active and (@ad<"20020912" @rlad<"20020912")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/12 13:54
S12 0	2	("6072981").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/12 13:54